

# INA5002AP1-TH51

For low frequency power amplify  
Silicon PNP Epitaxial

AEC-Q101 Compliance

## DESCRIPTION

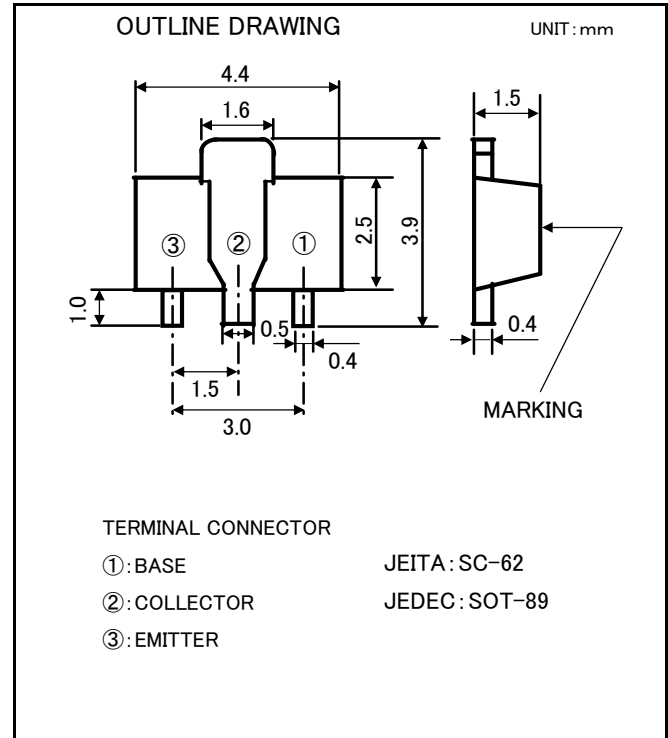
INA5002AP1 is a silicon PNP epitaxial transistor designed for relay drive or Power supply application.

## FEATURE

- Small package for easy mounting.
- High voltage  $V_{CE0} = -60V$
- High collector current  $I_C = -3A$
- Low  $V_{CE(sat)}$   $V_{CE(sat)} = -0.6V$  max (@  $I_C = -3A$  /  $I_E = -300mA$ )
- High collector dissipation  $P_C = 500mW$

## APPLICATION

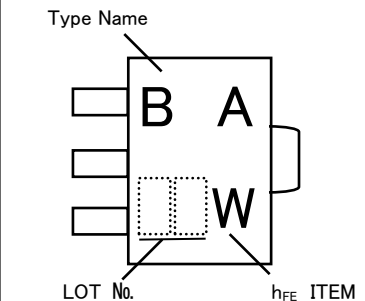
DC-DC converter, Relay drive, Motor drive



## MAXIMUM RATING ( $T_a = 25^\circ C$ )

SYMBOL	PARAMETER	RATING	UNIT
$V_{CBO}$	Collector to Base voltage	-80	V
$V_{EBO}$	Emitter to Base voltage	-6	V
$V_{CEO}$	Collector to Emitter voltage	-60	V
$I_C$	Collector current	-3	A
$I_{CM}$	Peak Collector current	-6	
$P_C$	Collector dissipation ( $T_a = 25^\circ C$ )	500	mW
$T_j$	Junction temperature	+150	$^\circ C$
$T_{stg}$	Storage temperature	-55 ~ +150	$^\circ C$

## MARKING



## ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

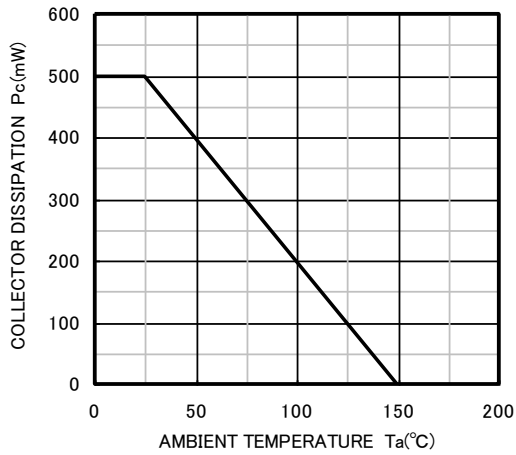
SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
$V_{(BR)CBO}$	C to B breakdown voltage	$I_C = -100 \mu A$ , $I_E = 0mA$	-80	-	-	V
$V_{(BR)EBO}$	E to B breakdown voltage	$I_E = -100 \mu A$ , $I_C = 0mA$	-6	-	-	V
$V_{(BR)CEO}$	C to E breakdown voltage	$I_C = -1mA$ , $R_{BE} = \infty$	-60	-	-	V
$I_{CBO}$	Collector cut off current	$V_{CB} = -60V$ , $I_E = 0mA$	-	-	-1.0	$\mu A$
$I_{EBO}$	Emitter cut off current	$V_{EB} = -4V$ , $I_C = 0mA$	-	-	-1.0	$\mu A$
$h_{FE}$	DC forward current gain	$V_{CE} = -2V$ , $I_C = -0.5A$	100	-	300	-
$V_{CE(sat)}$	C to E saturation voltage	$I_C = -3A$ , $I_B = -300mA$	-	-	-0.5	V
$f_r$	Gain band width product	$V_{CE} = -5V$ , $I_E = 100mA$	-	200	-	MHz
$C_{ob}$	Collector output capacitance	$V_{CB} = -10V$ , $I_E = 0mA$ , $f = 1MHz$	-	25	-	pF

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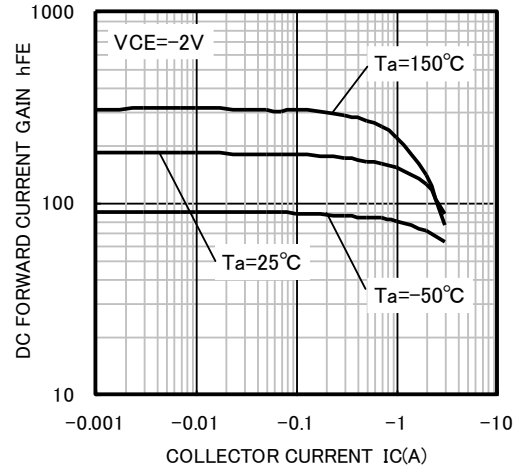
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## TYPICAL CHARACTERISTICS

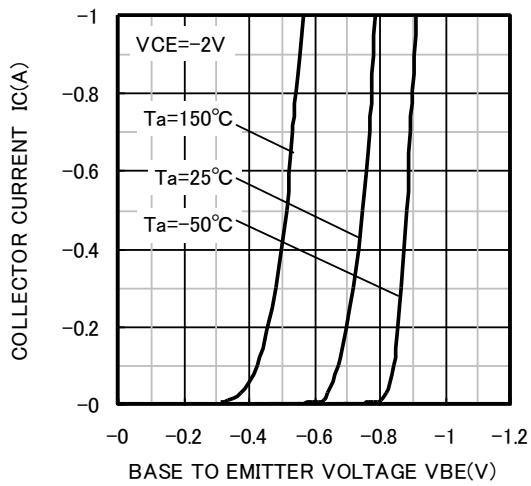
COLLECTOR DISSIPATION  
VS. AMBIENT TEMPERATURE



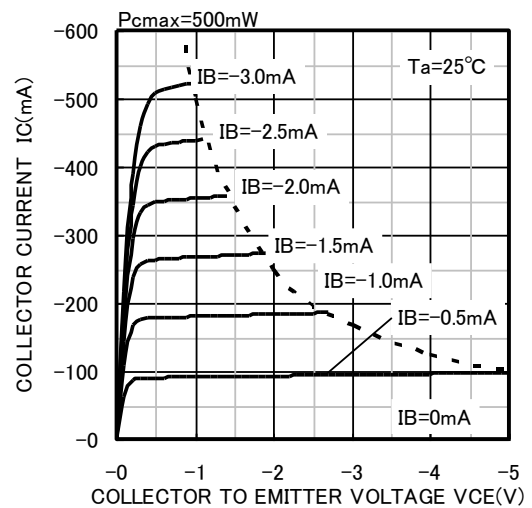
DC FORWARD CURRENT GAIN  
VS. COLLECTOR CURRENT



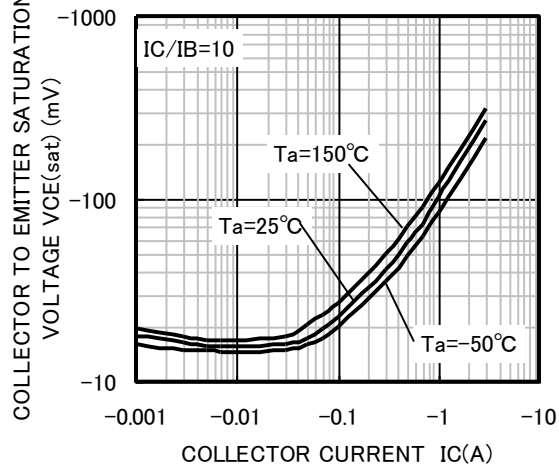
COMMON EMITTER TRANSFER



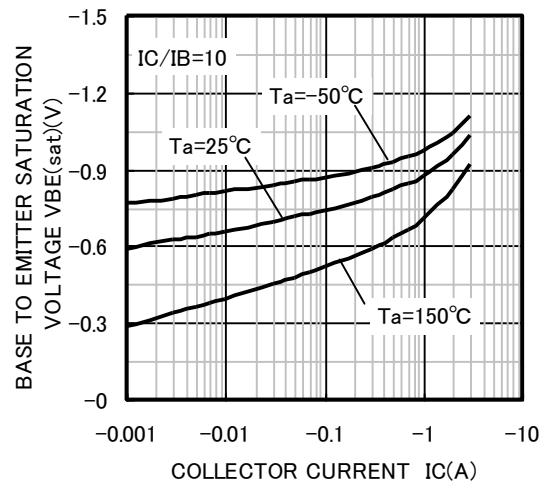
COMMON EMITTER OUTPUT



COLLECTOR TO EMITTER SATURATION VOLTAGE  
VS. COLLECTOR CURRENT

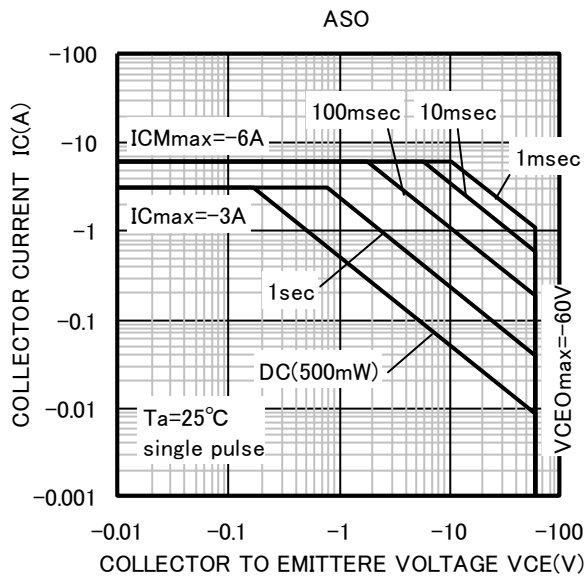
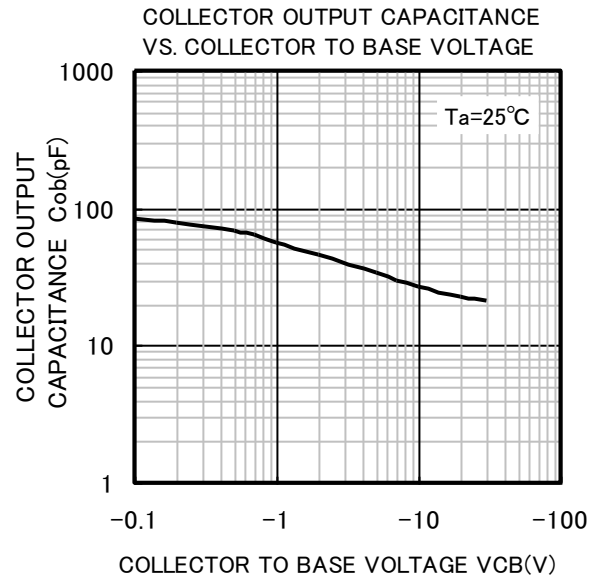
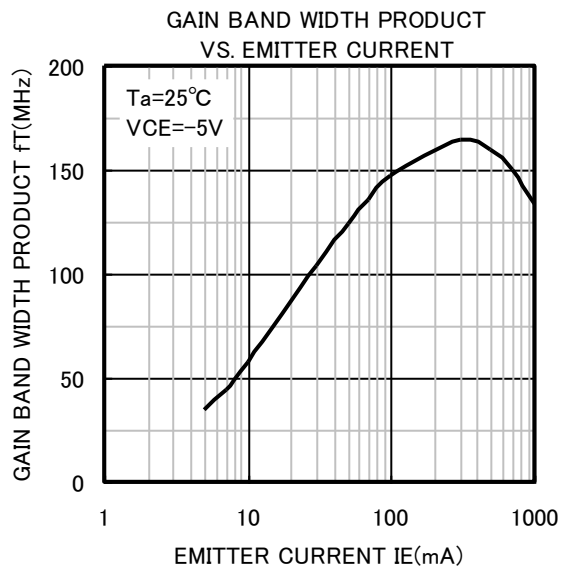


BASE TO EMITTER SATURATION VOLTAGE  
VS. COLLECTOR CURRENT



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